

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

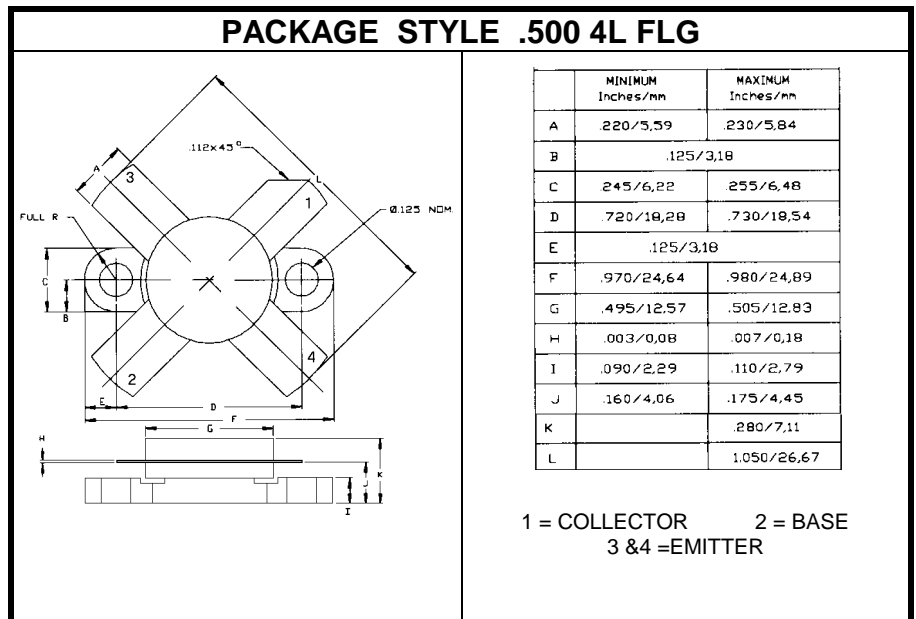
The **ASI THA15** is a Common Emitter Device Designed for SSB communications Applications.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	10 A
V_{CB}	110 V
V_{CE}	55 V
P_{DISS}	233 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.75 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA	55			V
BV_{CES}	I _C = 100 mA	110			V
BV_{CBO}	I _C = 100 mA	110			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _{CE} = 60 V			5.0	mA
I_{CEO}	V _{CE} = 30 V			5.0	mA
h_{FE}	V _{CE} = 6.0 V I _C = 1.4 A	15		50	---
C_{ob}	V _{CB} = 50 V f = 1.0 MHz			220	pF
P_G	V _{CE} = 50 V I _{cq} = 100 mA f = 30 MHz P _{out} = 150 W (PEP)	14			dB
IMD₃				-30	dBc
η_C			37		%